

ABSTRACT OF THE DISCLOSURE

A wafer producing method for producing a hexagonal single crystal wafer from a hexagonal single crystal ingot is disclosed. The wafer producing method includes a separation start point forming step of setting the focal point of a laser beam having a transmission wavelength to the ingot inside the ingot at a predetermined depth from the upper surface of the ingot. The separation start point forming step includes a first step of forming the separation start point with a first power and a second step of setting the focal point at the modified layer previously formed in the first step and then applying the laser beam to the ingot with a second power higher than the first power at an increased repetition frequency in the condition where the energy per pulse of the laser beam is the same as that in the first step, thereby separating the cracks from the modified layer.

(Fig. 11A)